

Bipolar Transistor

(-)100 V, (-)1 A, Low V_{CE}(sat), (PNP)NPN Single PCP

2SA1416, 2SC3646

Features

- Adoption of FBET and MBIT Processes
- High Breakdown Voltage and Large Current Capacity
- Fast Switching Speed
- Ultrasmall Size Making it Easy to Provide High-Density Small-Sized Hybrid IC's
- These Devices are Pb-Free and are RoHS Compliant

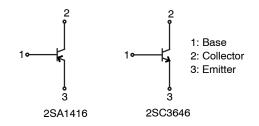
SPECIFICATIONS (): 2SA1416 ABSOLUTE MAXIMUM RATINGS at Ta = 25°C

Parameter	Symbol	Value	Unit
Collector to Base Voltage	V _{CBO}	(-) 120	V
Collector to Emitter Voltage	V _{CEO}	(-) 100	V
Emitter to Base Voltage	V _{EBO}	(-) 6	V
Collector Current	Ic	(-) 1	Α
Collector Current (Pulse)	I _{CP}	(-) 2	Α
Collector Dissipation	P _C	500	mW
Collector Dissipation (Note 1)		1.3	W
Junction Temperature	TJ	150	∘C
Storage Temperature	T _{STG}	–55 to +150	∘C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface mounted on ceramic substrate (250 mm² x 0.8 mm).

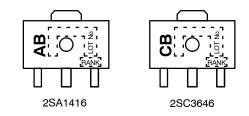
ELECTRICAL CONNECTION





SOT-89 / PCP-1 CASE 419AU

MARKING DIAGRAM



ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

ELECTRICAL CHARACTERISTICS at $T_A = 25^{\circ}C$

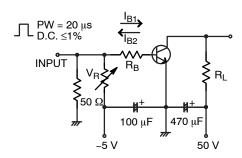
			Ratings			
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector Cutoff Current	I _{CBO}	V _{CB} = (-)100 V, I _E = 0 A			(-)100	nA
Emitter Cutoff Current	I _{EBO}	V _{EB} = (-)4V, I _C = 0 A			(-)100	nA
DC Current Gain	h _{FE}	V _{CE} = (-)5 V, I _C = (-)100 mA	15 V, 100* 00 mA		400*	
Gain-Bandwidth Product	f _T	V _{CE} = (-)10 V, I _C = (-)100 mA		120		MHz
Output Capacitance	Cob	V _{CB} = (-)10 V, f = 1 MHz		(13)8.5		pF
Collector to Emitter Saturation Voltage	V _{CE} (sat)	I _C = (-)400 mA, I _B = (-)40 mA		(-0.2)0.1	(-0.6)0.4	V
Base to Emitter Saturation Voltage	V _{BE} (sat)	I _C = (-)400 mA, I _B = (-)-40 mA		(-)0.85	(-)1.2	V
Collector to Base Breakdown Voltage	V _{(BR)CBO}	$I_C = (-)10 \mu A, I_E = 0 A$	(-)120			V
Collector to Emitter Breakdown Voltage	V _{(BR)CEO}	I_C = (-)1 mA, R_{BE} = ∞	(-)100			V
Emitter to Base Breakdown Voltage	V _{(BR)EBO}	$I_E = (-)10 \mu A, I_C = 0 A$	(-)6			V
Turn-On Time	t _{on}	See specified		(80)80		ns
Storage Time	t _{stg}	Test Circuit		(700)850		ns
Fall Time	t _f] [(40)50		ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

*The 2SA1416/2SC3646 are classified by 100 mA h_{FE} as follows:

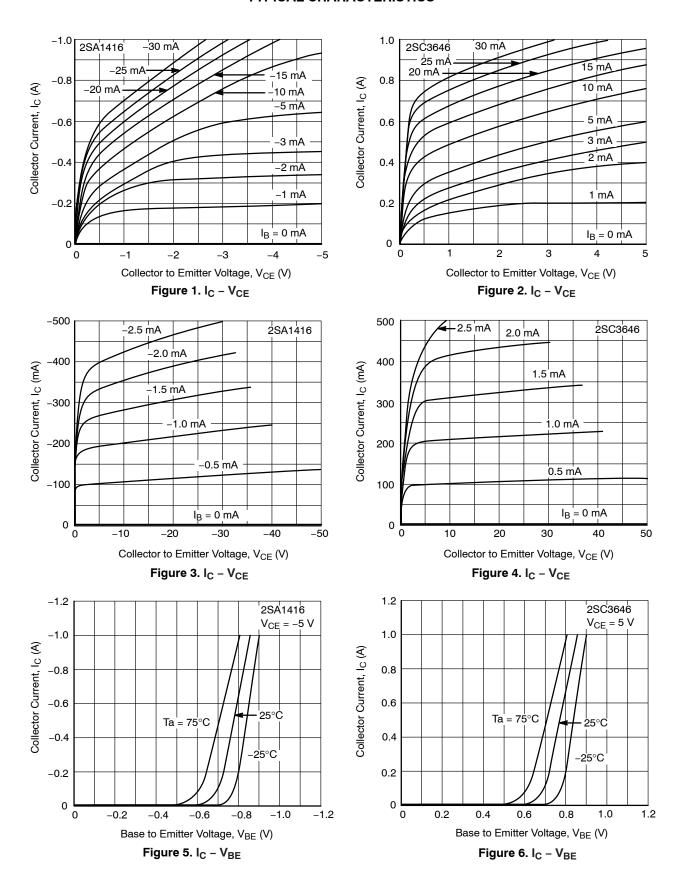
Rank	R	S	Т
h _{FE}	100 to 200	140 to 280	200 to 400

Switching Time Test Circuit

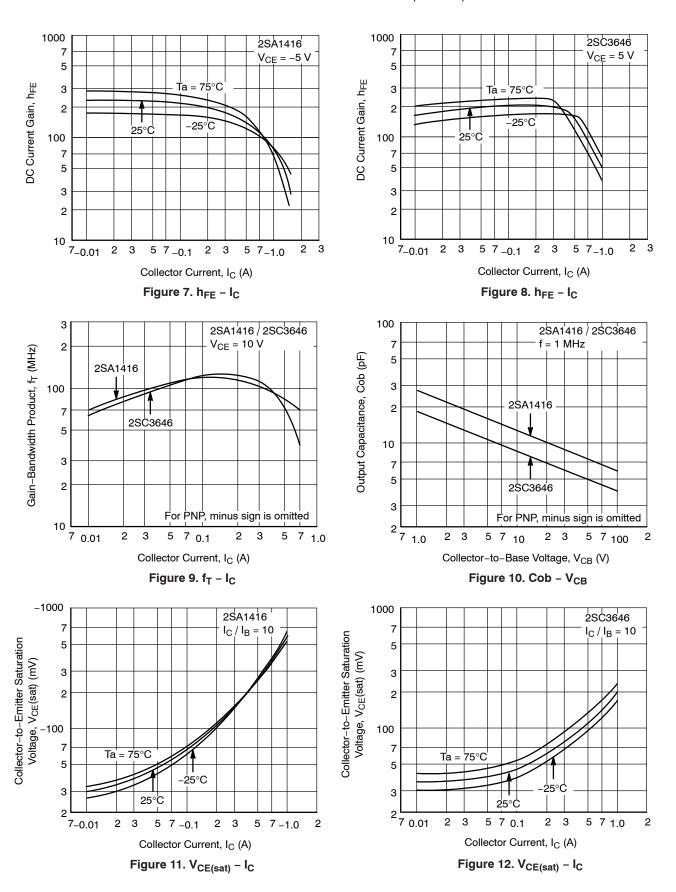


 $I_C = 10 I_{B1} = -10 I_{B2} = 400 \text{ mA}$ (For PNP, the polarity is reversed)

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS (continued)



TYPICAL CHARACTERISTICS (continued)

Base-to-Emitter

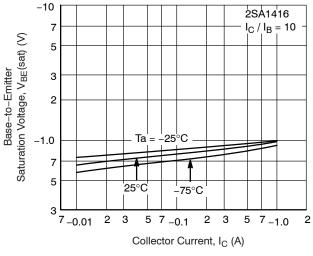


Figure 13. V_{BE}(sat) - I_C

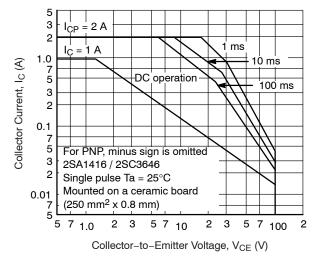


Figure 15. ASO

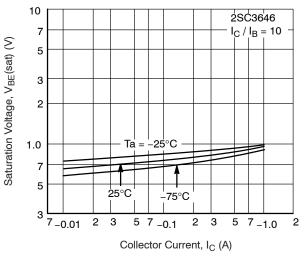


Figure 14. V_{BE}(sat) - I_C

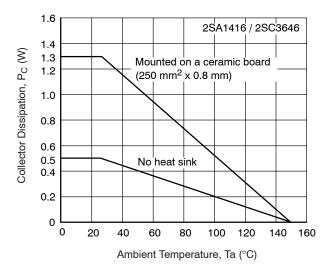


Figure 16. P_C – Ta

ORDERING INFORMATION

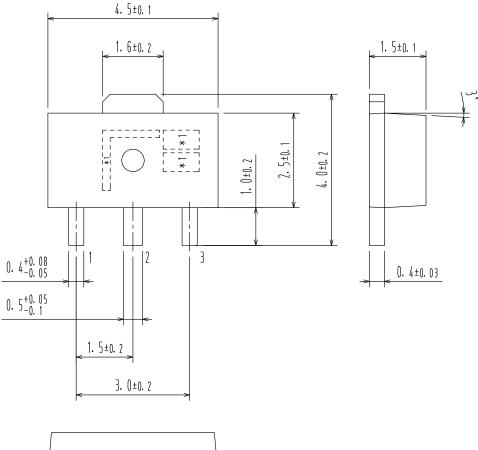
Device	Marking	Package	Shipping [†]	
2SA1416S-TD-E	AB	SOT-89 / PCP-1 (Pb-Free)	1000 / Tape & Reel	
2SA1416T-TD-E		(1.5.1.00)		
2SC3646S-TD-E	СВ			
2SC3646T-TD-E				

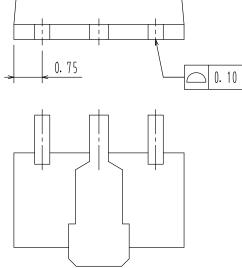
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ON

SOT-89 / PCP-1 CASE 419AU ISSUE O

DATE 30 APR 2012





DOCUMENT NUMBER:	98AON79746E	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-89 / PCP-1		PAGE 1 OF 1	

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warrantly, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer pu

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT: Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative